

BZT52C2V4S THRU BZT52C75S
PLASTIC-ENCAPSULATE ZENER DIODE



VOLTAGE 2.4~75 Volts **POWER** 200 mW

SOD-323 **Marking and Polarity**

FEATURES

- Low Zener Impedance
- Power Dissipation of 200mW
- High Stability and High Reliability
- Zener Voltage Tolerance: ± 5%(C Series)

MECHANICAL DATA

Package: SOD-323
Epoxy UL: 94V-0
Mounting position: Any
Weight: approx. 0.004g

Remark:

- ①. xx=Modle code,xx=WX~X5
- ②. White band denotes cathode

Maximum Ratings & Thermal Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

Parameter	Symbol	Value	Unit
Power Dissipation (Note1)	P _D	200	mW
Maximum instantaneous forward voltage@I _F =10mA (Note2)	V _F	1.0	V
Operating Temperature Range	T _{OPR}	-55~+150	°C
Storage temperature range	T _{STG}	-55~+150	°C
Thermal Resistance, Junction to Ambient Air	R _{θJA}	400 (Note1)	°C/W

- Notes: 1. Device mounted on ceramic PCB; 7.6mm x 9.4mm x 0.87mm with pad areas 25mm²
2. Pulse width < 10 ms

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Electrical Characteristics (Ratings at 25°C ambient temperature unless otherwise specified).

Device	Marking	Zener Voltage Range				Maximum Zener Impedance			Maximum Reverse Current	
		V _z @I _{zt}			I _{zt}	Z _{zt} @I _{zt}	Z _{zk} @I _{zk}	I _{zk}	IR	VR
		Min(V)	Nom(V)	Max(V)	mA	Ω		mA	uA	V
BZT52C2V4S	WX	2.28	2.4	2.52	5	100	600	1.0	50	1.0
BZT52C2V7S	W1	2.57	2.7	2.84	5	100	600	1.0	20	1.0
BZT52C3V0S	W2	2.85	3.0	3.15	5	95	600	1.0	10	1.0
BZT52C3V3S	W3	3.14	3.3	3.47	5	95	600	1.0	5	1.0
BZT52C3V6S	W4	3.42	3.6	3.78	5	90	600	1.0	5	1.0
BZT52C3V9S	W5	3.71	3.9	4.10	5	90	600	1.0	3	1.0
BZT52C4V3S	W6	4.09	4.3	4.52	5	90	600	1.0	3	1.0
BZT52C4V7S	W7	4.47	4.7	4.94	5	80	500	1.0	3	2.0
BZT52C5V1S	W8	4.85	5.1	5.36	5	60	480	1.0	2	2.0
BZT52C5V6S	W9	5.32	5.6	5.88	5	40	400	1.0	1	2.0
BZT52C6V2S	WA	5.89	6.2	6.51	5	10	150	1.0	3	4.0
BZT52C6V8S	WB	6.46	6.8	7.14	5	15	80	1.0	2	4.0
BZT52C7V5S	WC	7.13	7.5	7.88	5	15	80	1.0	1	5.0
BZT52C8V2S	WD	7.79	8.2	8.61	5	15	80	1.0	0.7	5.0
BZT52C9V1S	WE	8.65	9.1	9.56	5	15	100	1.0	0.5	6.0
BZT52C10S	WF	9.50	10.0	10.50	5	20	150	1.0	0.2	7.0
BZT52C11S	WG	10.45	11.0	11.55	5	20	150	1.0	0.1	8.0
BZT52C12S	WH	11.40	12.0	12.60	5	25	150	1.0	0.1	8.0
BZT52C13S	WI	12.35	13.0	13.65	5	30	170	1.0	0.1	8.0
BZT52C15S	WJ	14.25	15.0	15.75	5	30	200	1.0	0.1	10.5
BZT52C16S	WK	15.20	16.0	16.80	5	40	200	1.0	0.1	11.2
BZT52C18S	WL	17.10	18.0	18.90	5	45	225	1.0	0.1	12.6
BZT52C20S	WM	19.00	20.0	21.00	5	55	225	1.0	0.1	14.0
BZT52C22S	WN	20.90	22.0	23.10	5	55	250	1.0	0.1	15.4
BZT52C24S	WO	22.80	24.0	25.20	5	70	250	1.0	0.1	16.8
BZT52C27S	WP	25.65	27.0	28.35	2	80	300	0.5	0.1	18.9
BZT52C30S	WQ	28.50	30.0	31.50	2	80	300	0.5	0.1	21.0
BZT52C33S	WR	31.35	33.0	34.65	2	80	325	0.5	0.1	23.1
BZT52C36S	WS	34.20	36.0	37.80	2	90	350	0.5	0.1	25.2
BZT52C39S	WT	37.05	39.0	40.95	2	130	350	0.5	0.1	27.3
BZT52C43S	WU	40.85	43.0	45.15	2	130	350	0.5	0.1	29.4
BZT52C47S	WV	44.65	47.0	49.35	2	170	1000	0.25	0.1	36.0
BZT52C51S	X1	48.45	51.0	53.55	2	180	1300	0.25	0.1	39.0
BZT52C56S	X2	53.20	56.0	58.80	2	200	1400	0.25	0.1	43.0
BZT52C62S	X3	58.90	62.0	65.10	2	225	1400	0.25	0.1	47.0
BZT52C68S	X4	64.60	68.0	71.40	2	240	1600	0.25	0.1	52.0
BZT52C75S	X5	71.25	75.0	78.75	2	265	1700	0.25	0.1	56.0

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RATING AND CHARACTERISTIC CURVES

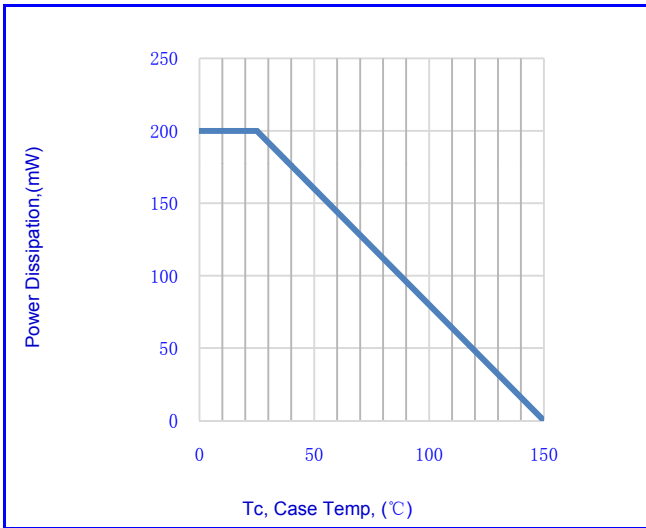


Fig.1-POWER DISSIPATION VS. AMBIENT TEMP.

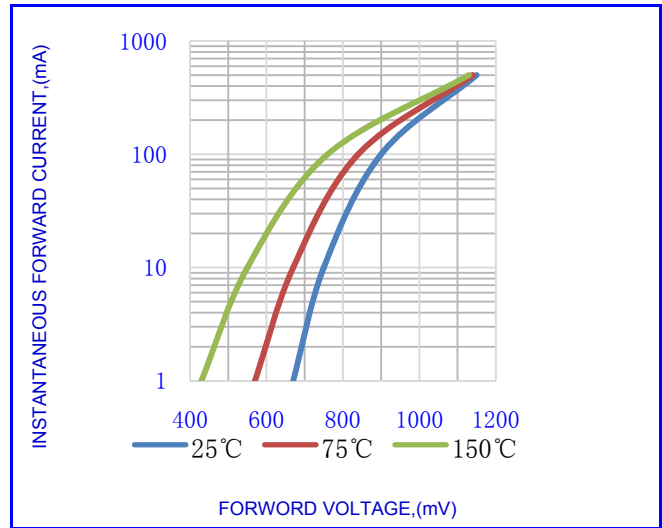


Fig.2- Forward characteristics

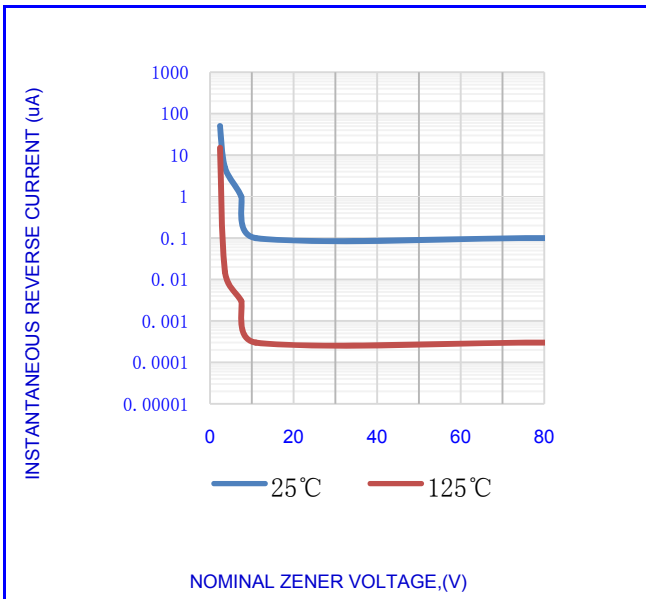


Fig.3- TYPICAL REVERSE CHARACTERISTICS

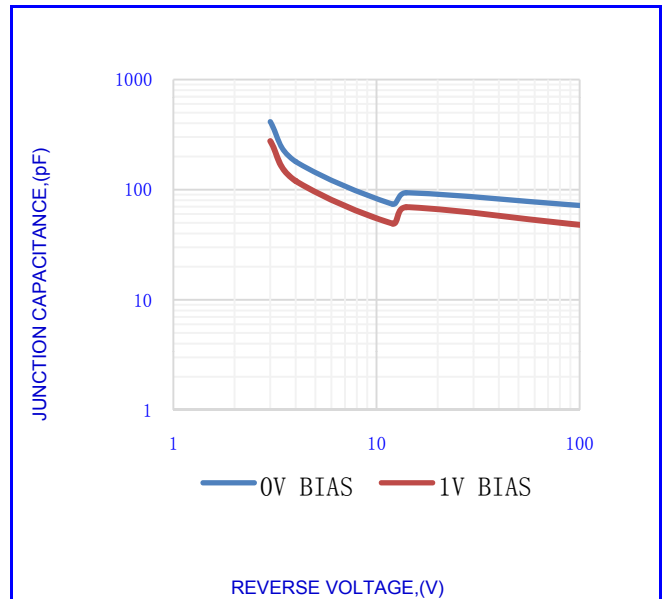


Fig.4- TYPICAL JUNCTION CAPACITANCE

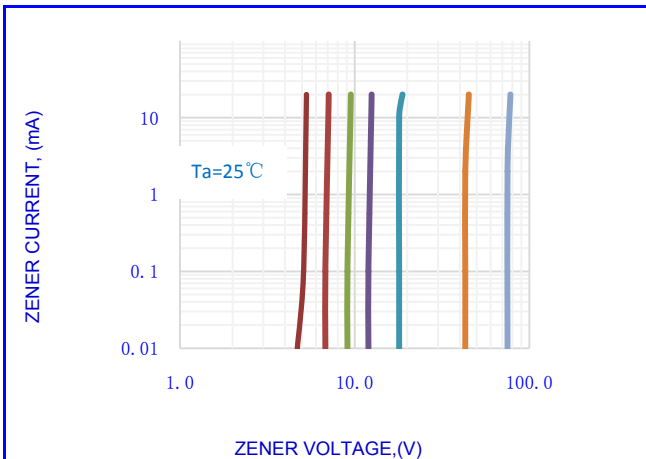


Fig.5-ZENER BREAKDOWN CHARACTERISTICS

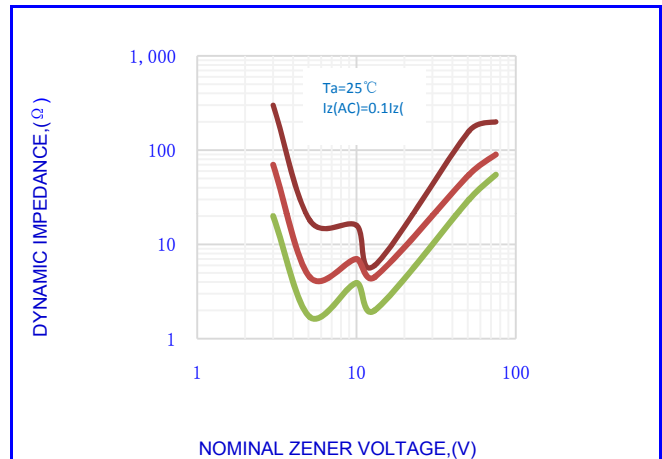


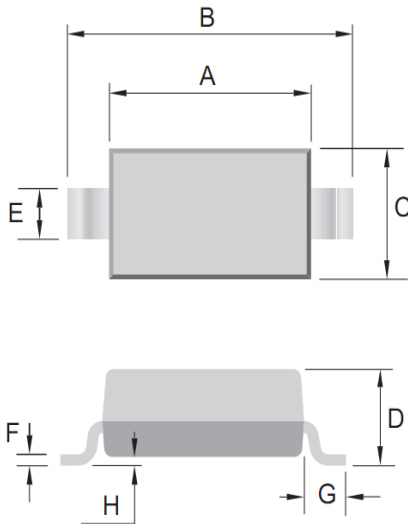
Fig.6-EFFECT OF ZENER VOLTAGE ON ZENER IMPEDANCE

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OUTLINE DRAWINGS

SOD-323



OUTLINE DIMENSIONS						
Dim.	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.600	-	1.800	0.063	-	0.071
B	2.400	-	2.700	0.094	-	0.106
C	1.200	-	1.400	0.047	-	0.055
D	-	-	1.000	-	-	0.039
E	0.250	-	0.350	0.010	-	0.014
F	0.080	-	0.150	0.003	-	0.006
G	-	0.475	-	-	0.019	-
H	-	-	0.120	-	-	0.005

MOUNTING PAD LAYOUT

SOD-323



OUTLINE DIMENSIONS						
Dim.	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	--	2.900	--	--	0.114	--
B	--	0.500	--	--	0.020	--
C	--	1.440	--	--	0.057	--
D	--	0.730	--	--	0.029	--

Packing Information

Package	Pack	Reel Size (mm)	Quantity (pcs/reel)	Inner Box Size L×W×H(mm)	Carton Size L×W×H(mm)	Quantity (Inner Box/carton)
SOD-323	T/R	Φ180	3000	210×208×203	440×440×230	4

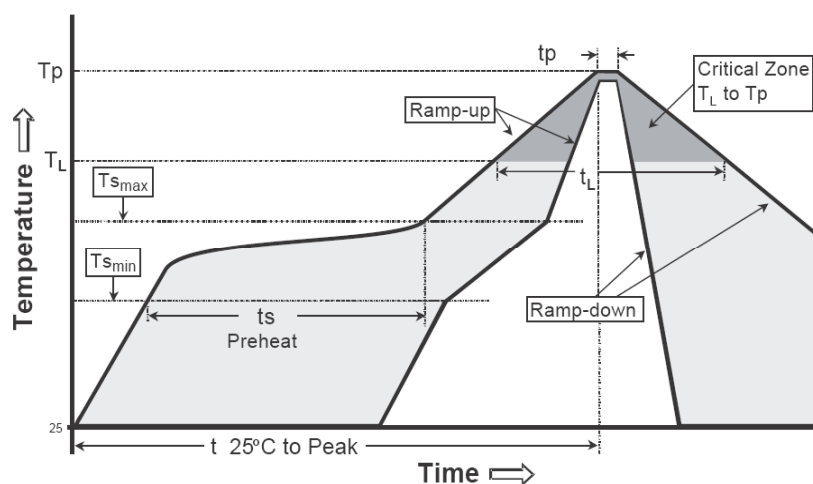
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Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat -Temperature Min(TS min) -Temperature Max(TS max) -Time(ts min to ts max)	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
Time maintained above: -Temperature (TL) - Time (tL)	183°C 60-150 seconds	217°C 60-150 seconds
Peak Temperature(TP)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

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